

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

ROBERT H. HAVEMANN ET AL.

Serial No. 09/216,214 (TI-21570)

Filed December 18, 1998

For: ENHANCEMENT TO POLYSILICON GATE

Art Unit 2811

Examiner T. Tran

Commissioner for Patents
Washington, D. C. 20231

Sir:

PRELIMINARY AMENDMENT

Prior to the first Office action in the subject CPA, please amend the above identified application as follows:

In the claims:

Cancel claims 3 to 7 without prejudice.

Add the following claims:

10. A transistor structure which comprises:
- a region of semiconductor material having a gate dielectric thereover;
 - a polysilicon gate disposed over said gate dielectric having a top and sidewalls;
 - source/drain regions in said region of semiconductor material spaced apart from each other and each disposed adjacent a said polysilicon gate sidewall; and

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